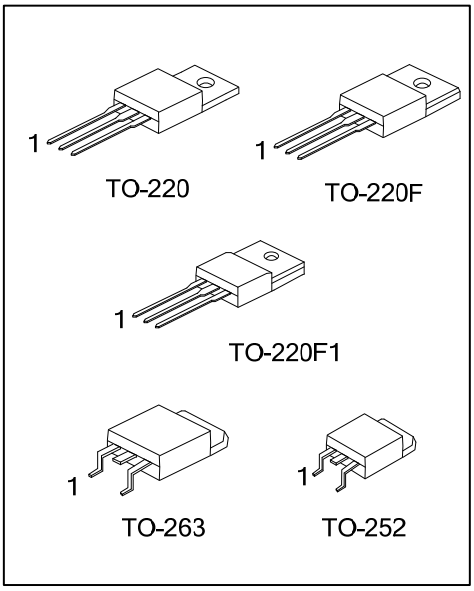
15NM65

Power MOSFET

15A, 650V N-CHANNEL SUPER-JUNCTION MOSFET



■ DESCRIPTION

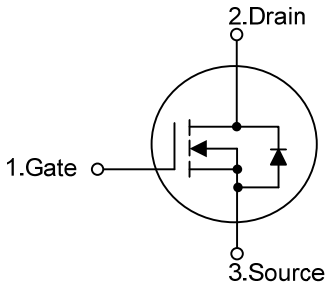
The UTC **15NM65** is a Super Junction MOSFET Structure. It uses UTC advanced planar stripe, DMOS technology to provide customers perfect switching performance, minimal on-state resistance.

The UTC **15NM65** is universally applied in electronic lamp ballasts based on half bridge topology, high efficiency switched mode power supplies, active power factor correction, etc.

■ FEATURES

* $R_{DS(ON)} \leq 0.35\Omega$ @ V_{GS}=10V, I_D=7.5A
* By using Super Junction Structure
* Fast Switching
* With 100% Avalanche Tested

■ SYMBOL



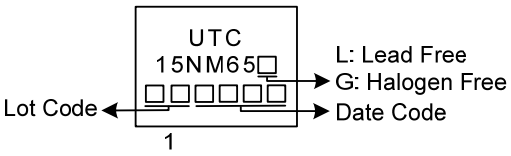
■ ORDERING INFORMATION

Ordering Number		Package	Pin Assignment			Packing
Lead Free	Halogen Free		1	2	3	
15NM65L-TA3-T	15NM65G-TA3-T	TO-220	G	D	S	Tube
15NM65L-TF3-T	15NM65G-TF3-T	TO-220F	G	D	S	Tube
15NM65L-TF1-T	15NM65G-TF1-T	TO-220F1	G	D	S	Tube
15NM65L-TN3-R	15NM65G-TN3-R	TO-252	G	D	S	Tape Reel
15NM65L-TQ2-T	15NM65G-TQ2-T	TO-263	G	D	S	Tube
15NM65L-TQ2-R	15NM65G-TQ2-R	TO-263	G	D	S	Tape Reel

Note: Pin Assignment: G: Gate D: Drain S: Source

15NM65G-TA3-T (1) Packing Type (2) Package Type (3) Green Package	(1) T: Tube, R: Tape Reel (2) TA3: TO-220, TF1: TO-220F1, TF3: TO-220F, TN3: TO-252, TQ2: TO-263 (3) G: Halogen Free and Lead Free, L: Lead Free

■ MARKING



■ ABSOLUTE MAXIMUM RATINGS (T_C = 25°C, unless otherwise specified)

PARAMETER		SYMBOL	RATINGS	UNIT
Drain-Source Voltage		V_{DSS}	650	V
Gate-Source Voltage		V_{GSS}	±30	V
Drain Current	Continuous	I_D	15	A
	Pulsed (Note 2)	I_{DM}	60	A
Avalanche Current (Note 2)		I_{AR}	2.7	A
Avalanche Energy	Single Pulsed (Note 3)	E_{AS}	485	mJ
Peak Diode Recovery dv/dt (Note 4)		dv/dt	4.5	V/ns
Power Dissipation	TO-220/TO-263	P_D	140	W
	TO-220F/TO-220F1		32	W
	TO-252		85	W
Junction Temperature		T_J	+150	°C
Storage Temperature		T_{STG}	-55 ~ +150	°C

Notes: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.
2. Repetitive Rating : Pulse width limited by maximum junction temperature.
3. L = 133 mH, I_{AS} = 2.7A, V_{DD} = 50V, R_G = 25 Ω, Starting T_J = 25°C
4. I_{SD}≤15A, di/dt≤200A/μs, V_{DD}≤BV_{DSS}, Starting T_J = 25°C

■ THERMAL DATA

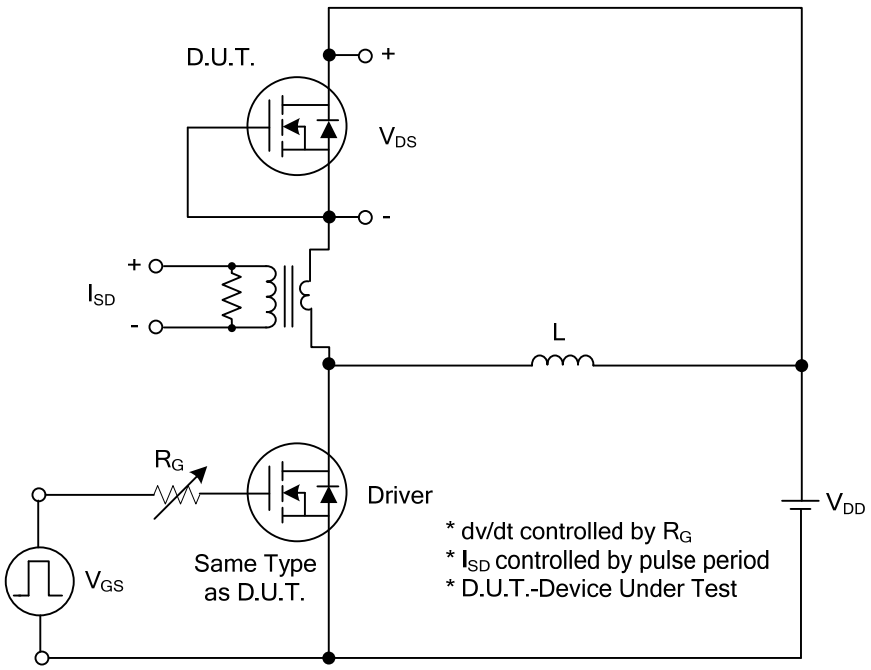
PARAMETER		SYMBOL	RATINGS	UNIT
Junction to Ambient	TO-220/TO-220F TO-220F1/TO-263	θ_{JA}	62.5	°C/W
	TO-252		110	°C/W
Junction to Case	TO-220/TO-263	θ_{JC}	0.89	°C/W
	TO-220F/TO-220F1		3.9	°C/W
	TO-252		1.5	°C/W

■ ELECTRICAL CHARACTERISTICS (T_J=25°C, unless otherwise specified)

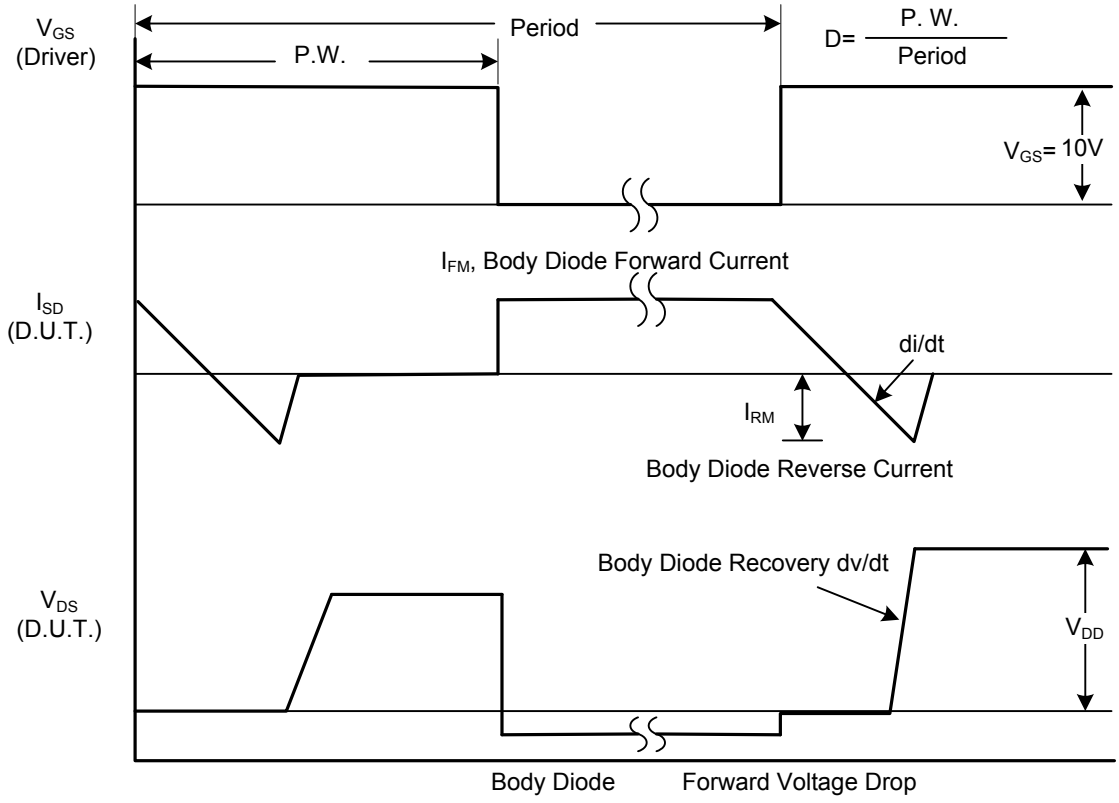
PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
OFF CHARACTERISTICS						
Drain-Source Breakdown Voltage	BV_{DSS}	V_{GS}=0V, I_D=250μA	650			V
Drain-Source Leakage Current	I_{DSS}	V_{DS}=650V, V_{GS}=0V			10	μA
Gate-Source Leakage Current	I_{GSS}	V_{DS}=0V ,V_{GS}=±30V			±100	nA
ON CHARACTERISTICS						
Gate Threshold Voltage	$V_{GS(TH)}$	V_{DS}= V_{GS}, I_D=250μA	2.5		4.5	V
Drain-Source On-State Resistance	$R_{DS(ON)}$	V_{GS}=10V, I_D=7.5A			0.35	Ω
DYNAMIC PARAMETERS						
Input Capacitance	C_{ISS}	V_{GS}=0V, V_{DS}=25V, f=1.0MHz		1100		pF
Output Capacitance	C_{OSS}			870		pF
Reverse Transfer Capacitance	C_{RSS}			96		pF
SWITCHING PARAMETERS						
Total Gate Charge (Note 1)	Q_G	V_{DS}=520V, V_{GS}=10V, I_D=15A , I_G=1mA (Note 1, 2)		40.5		nC
Gate-Source Charge	Q_{GS}			6		nC
Gate-Drain Charge	Q_{GD}			15		nC
Turn-ON Delay Time (Note 1)	$t_{D(ON)}$	V_{DD}=100V, I_D=15A, R_G=25Ω V_{GS}=10V (Note 1, 2)		14		ns
Turn-ON Rise Time	t_R			30		ns
Turn-OFF Delay Time	$t_{D(OFF)}$			138		ns
Turn-OFF Fall Time	t_F			63		ns
SOURCE- DRAIN DIODE RATINGS AND CHARACTERISTICS						
Maximum Body-Diode Continuous Current	I_S				15	A
Maximum Body-Diode Pulsed Current	I_{SM}				60	A
Drain-Source Diode Forward Voltage (Note 1)	V_{SD}	I_S =15A, V_{GS}=0V			1.4	V
Reverse Recovery Time (Note 1)	t_{rr}	I_S=15A, V_{GS}=0V, dI_F/dt=100A/μs		410		ns
Reverse Recovery Charge	Q_{rr}			6.95		μC

Notes: 1. Pulse Test : Pulse width ≤ 300μs, Duty cycle ≤ 2%.
2. Essentially independent of operating temperature.

■ TEST CIRCUITS AND WAVEFORMS

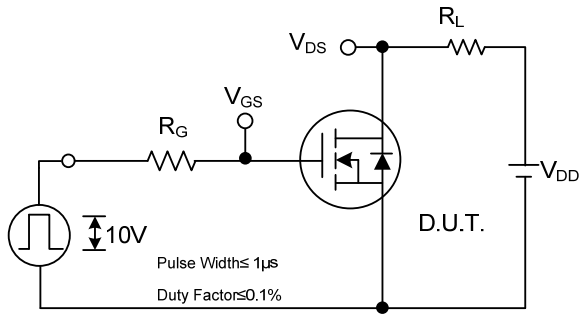


Peak Diode Recovery dv/dt Test Circuit

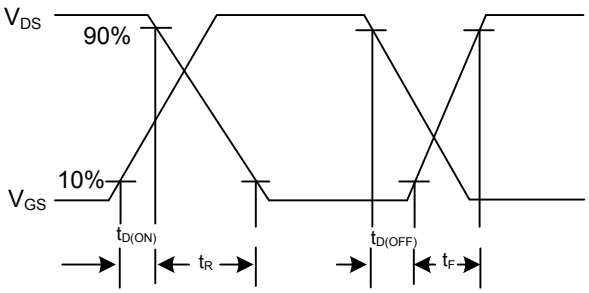


Peak Diode Recovery dv/dt Waveforms

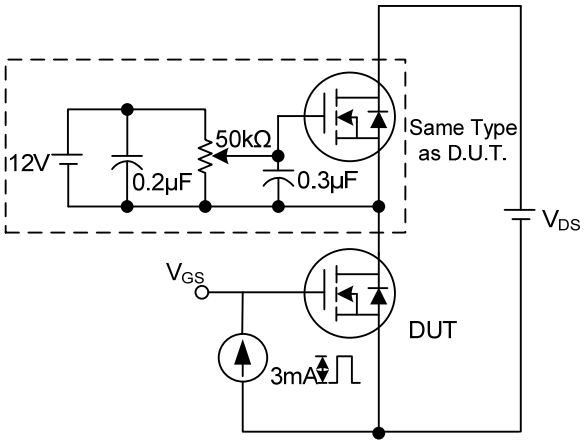
■ TEST CIRCUITS AND WAVEFORMS



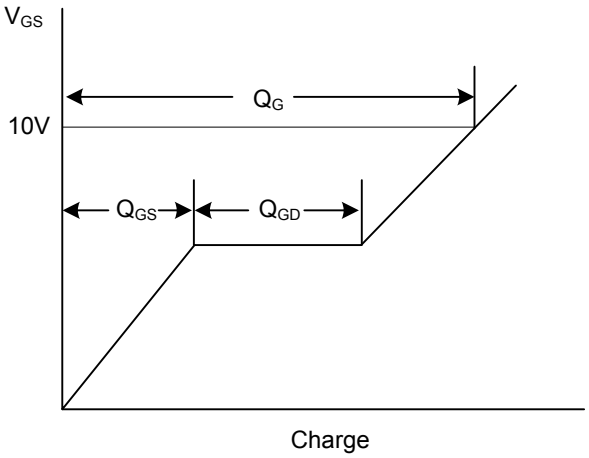
Switching Test Circuit



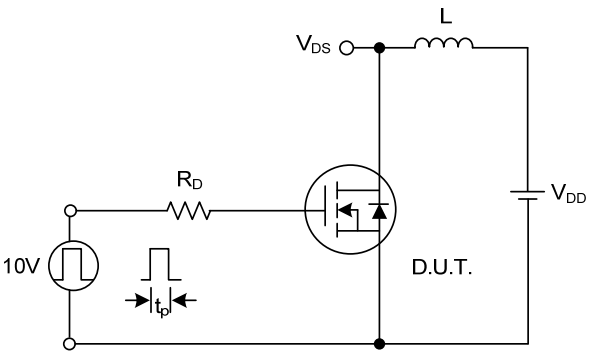
Switching Waveforms



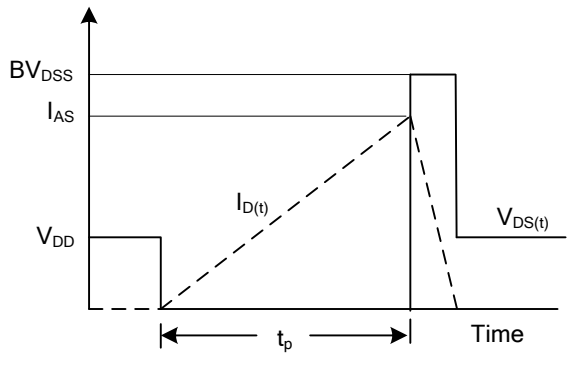
Gate Charge Test Circuit



Gate Charge Waveform



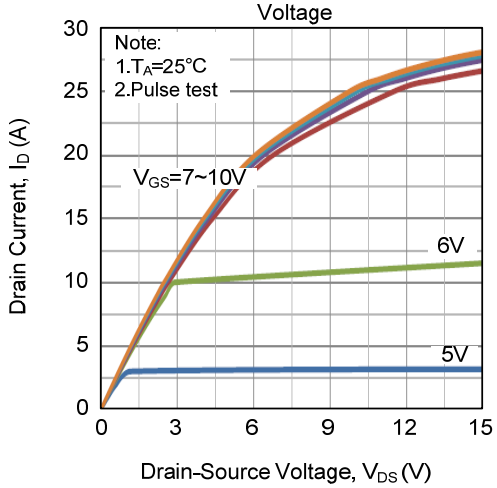
Unclamped Inductive Switching Test Circuit



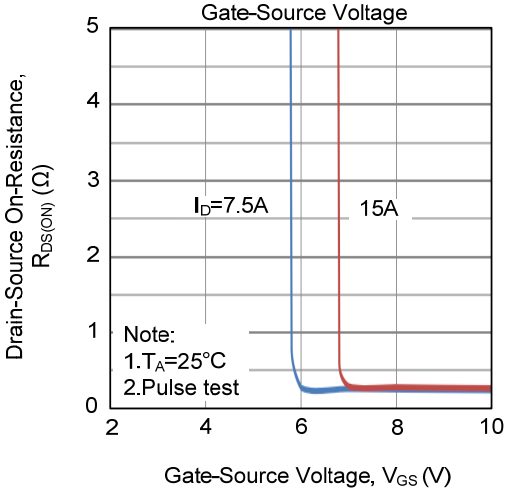
Unclamped Inductive Switching Waveforms

■ TYPICAL CHARACTERISTICS

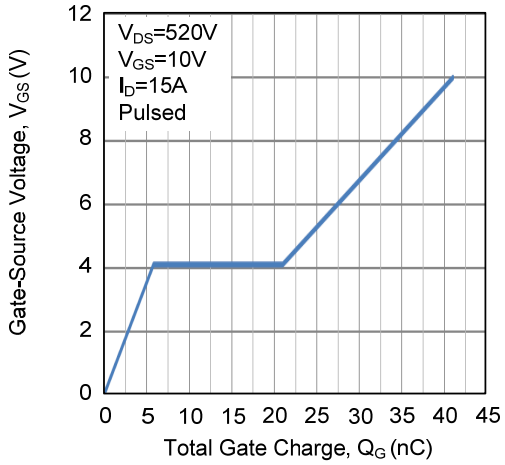
Drain Current vs. Drain-Source Voltage



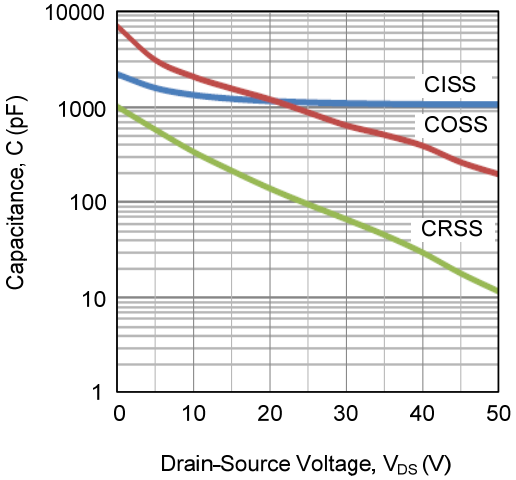
Drain-Source On-Resistance vs. Gate-Source Voltage



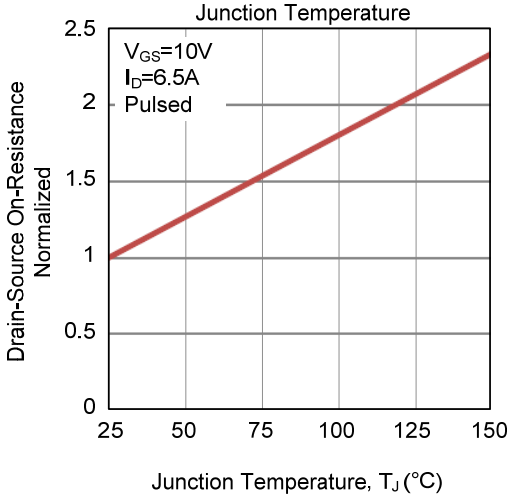
Gate Charge Characteristics



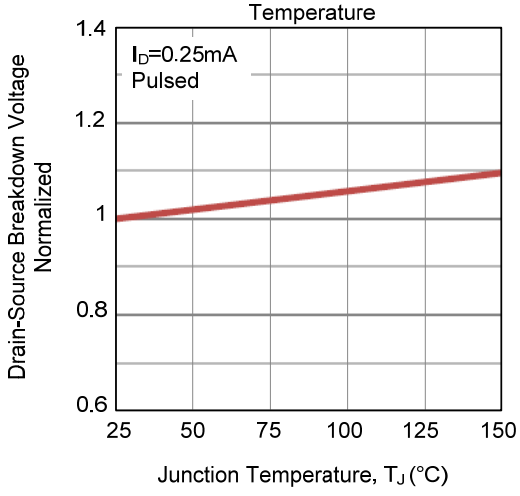
Capacitance Characteristics



Drain-Source On-Resistance vs. Junction Temperature

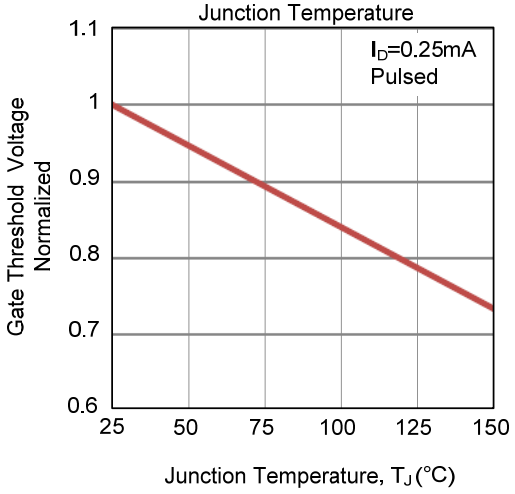


Breakdown Voltage vs. Junction Temperature

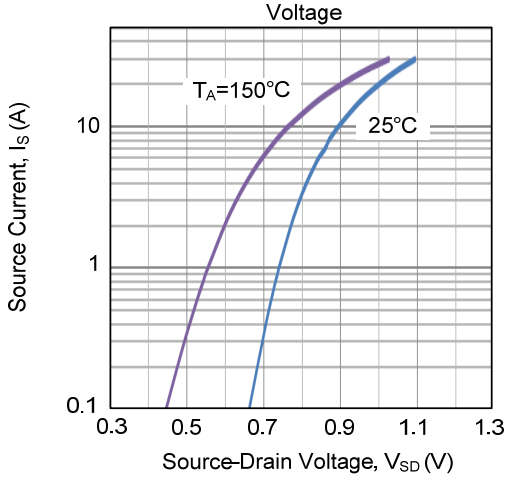


■ TYPICAL CHARACTERISTICS (Cont.)

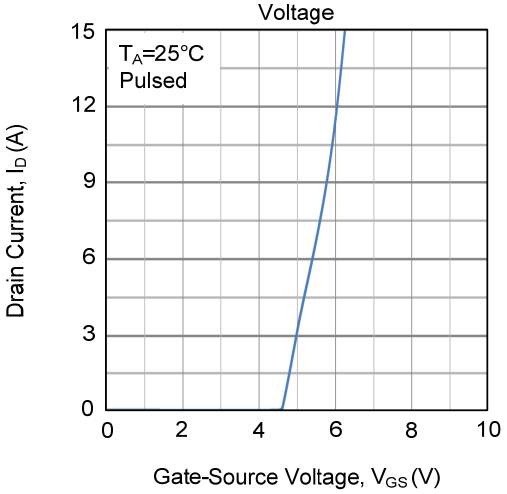
Gate Threshold Voltage vs. Junction Temperature



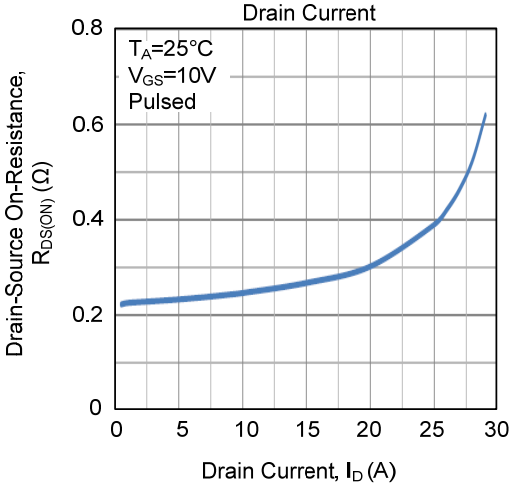
Source Current vs. Source-Drain Voltage



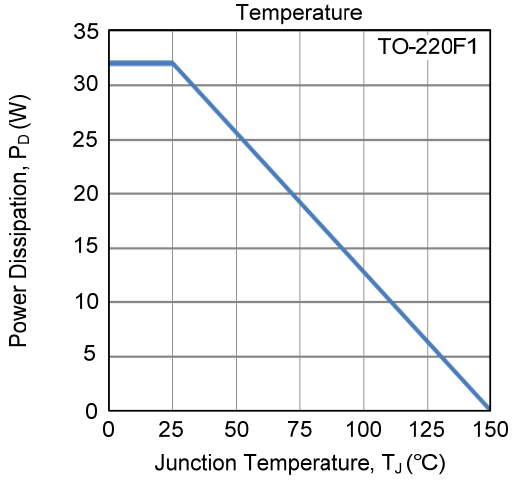
Drain Current vs. Gate-Source Voltage



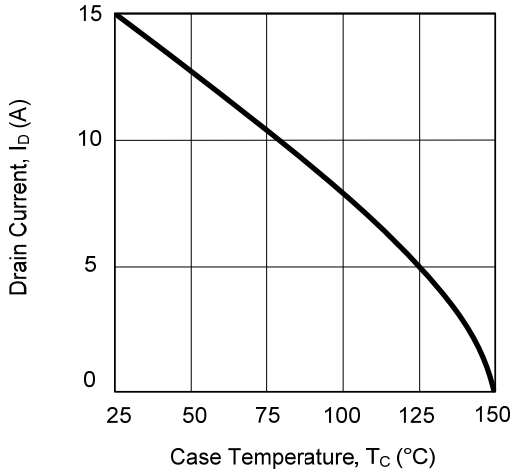
Drain-Source On-Resistance vs. Drain Current



Power Dissipation vs. Junction Temperature



Drain Current vs. Case Temperature



■ TYPICAL CHARACTERISTICS (Cont.)